

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI HF30-28S** is Designed for

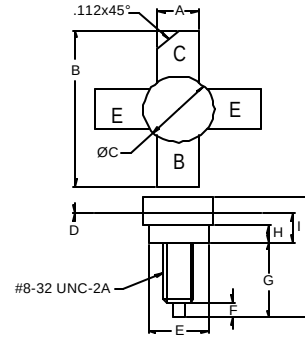
FEATURES:

- $P_G = 20$ dB min. at 30 W/30 MHz
- $IMD_3 = -30$ dBc max. at 30 W_(PEP)
- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	5.0 A
V_{CB}	65 V
V_{CE}	35 V
V_{EBO}	4.0 V
P_{DISS}	60 W @ $T_C = 25^\circ C$
T_J	$-65^\circ C$ to $+200^\circ C$
T_{STG}	$-65^\circ C$ to $+150^\circ C$
θ_{JC}	$2.9^\circ C/W$

PACKAGE STYLE .380 4L STUD



DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.220 / 5.59	.230 / 5.84
B	.980 / 24.89	
C	.370 / 9.40	.385 / 9.78
D	.004 / 0.10	.007 / 0.18
E	.320 / 8.13	.330 / 8.38
F	.100 / 2.54	.130 / 3.30
G	.450 / 11.43	.490 / 12.45
H	.090 / 2.29	.100 / 2.54
I	.155 / 3.94	.175 / 4.45
J		.750 / 19.05

ORDER CODE: ASI10605

CHARACTERISTICS $T_C = 25^\circ C$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	$I_C = 10$ mA	65		---	V
BV_{CES}	$I_C = 200$ mA	65		---	V
BV_{CEO}	$I_C = 200$ mA	35		---	V
BV_{EBO}	$I_E = 10$ mA	4.0		---	V
I_{CES}	$V_{CE} = 30$ V	---		10	mA
I_{CBO}	$V_{CE} = 30$ V	---		1.0	mA
h_{FE}	$V_{CE} = 5.0$ V $I_C = 500$ mA	5.0		200	---
C_{OB}	$V_{CB} = 30$ V $f = 1.0$ MHz	---		65	pF
G_P h_c	$V_{CE} = 28$ V $P_{IN} = 7.0$ W $f = 175$ MHz $P_{OUT} = 30$ W(PEP)	7.6 60		---	dB %